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Im pact of the Casim in-Polder Potential and Johnson Noise on Bose-Einstein Condensate Stability near Surfaces

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W e investigate the stability of magnetically trapped atom is Bose-E instein condensates and thermal clouds near the transition temperature at small distances 0.5 m d 10 m from a micro-fabricated silicon chip. For a 2 m thick copper lm the trap lifetime is limited by Johnson-noise induced currents and falls below 1 s at a distance of 4 m. A dielectric surface does not adversely a ect the sample until the attractive C asim in-Polder potential signi cantly reduces the trap depth.

B ose-E instein condensates in m agnetic traps [1, 2, 3, 4, 5] and w aveguides [3, 6], and therm allatom s in waveguides [7] produced by m icrofabricated structures (m icrotraps) hold great promise for new quantum devices for atom ic m atter waves, such as Fabry-P erot resonators [8], interferom eters [9], or Josephson junctions [10]. Full quantum control over the motion of an ultracold atom of m ass m and energy E requires potentials that vary abruptly on a length scale $h=(m E)^{l=2} = 1 m$. Such potentials can be created at sm all distances d from m iniaturized eld sources.

How ever, the proxim ity of a room -tem perature surface can perturb the ultracold gas, and m icrotrap experim ents have revealed condensate fragm entation [3, 4, 11], heating [1, 11], and reduced trap lifetim e [11]. The fragm entation has been traced to spatial variations of the longitudinalm agnetic eld near a conductor carrying current [12], while heating and loss have been elim inated for distances 70 m by careful electronic design and shielding [4]. However, Jones et al. [13] and Harber et al. [14] have recently reported a fundam ental limit due to spin ips induced by therm ally excited currents in a mesoscopic conductor, in very good agreem ent with theoretical predictions [15] over the m easurem ent regions 25 m d 100 m and 3 m d 1 mm, respectively.

In this Letter, we explore fundam ental lim itations on condensate stability at small distances down to d = m from dielectric and metal surfaces. For a 2 0:5 m thick copper lm carrying no current we observe a distance-dependent lifetim e (d) that is quantitatively explained by them alm agnetic eld uctuations arising from Johnson-noise induced currents [15, 16]. For the dielectric, we observe a reduction in trap lifetime only when the vicinity of the surface lim its the trap depth. A one-dimensional (1D) evaporation model can explain the m easured trap loss, but only when the attractive C asim ir-Polder force [17] between atom s and surface is included. Our results suggest that the local manipulation of condensates will be possible using thin conductors, which have low magnetic eld noise, on dielectric surfaces.

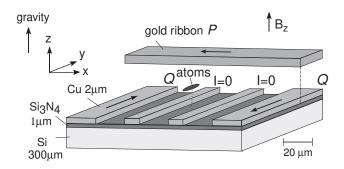


FIG.1: Microfabricated chip. (Only the x direction is to scale.) The outer Cu wires (Q) generate a 2D quadrupole eld in the xz plane. The ribbon (P) in combination with an external eld gradient creates the con nem ent along y.

The atom -surface interactions are studied using ultracold atoms con ned in a Io e-P ritchard trap generated by currents owing in microfabricated conductors on a silicon chip (see Fig. 1). The chip was produced by nst coating a 300 m thick silicon substrate with a 1 m thick, electrically insulating Si_3N_4 di usion barrier using plasm a-enhanced chem ical vapor deposition. Subsequently, a 20 nm thick T i adhesion layer, a 2.15(20) m thick C u conducting layer, a 40 nm thick T i, a 50 nm thick P d, and a 100 nm thick A u layer were deposited by electron beam evaporation. Finally, the wires were de ned by photolithography and wet etching.

The radial (xz) con nem ent of the Io e trap form ed above the chip is provided by a 2D quadrupole ekd, generated by two copper wires Q along the y direction carrying antiparallel currents, in superposition with a bias ekd along z. The centers of the 2 m thick and 20 m wide Q wires are separated by 100 m. The axial (y) con nem ent is created by a current-carrying gold ribbon P along x in combination with an external ekd gradient along y. The 25 m thick, 150 m wide ribbon 155 m above the chip was wire-bonded to the surface.

The condensate production starts with a standard m agneto-optical trap (MOT), into which typically 10^7 ⁸⁷Rb atom s are collected within 8 s from a Rb dispenser beam [2]. We then move the MOT cloud from the original distance d = 17 mm to within d = 6 mm of the chip surface, and compress it for 20 ms. A fler the MOT light has been extinguished, the atom s are optically pumped

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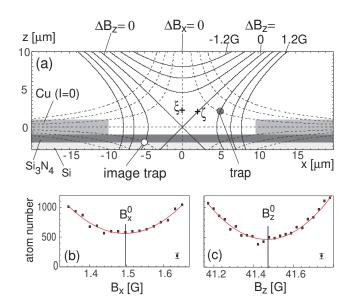


FIG.2: (a) M ap of relative eld (B $_x$; B $_z$) to trap position in the xz plane. D ashed (solid) lines are contours of B $_x$ (B $_z$), plotted with 0.4 G spacing. (b,c) M easured atom loss versus B $_x$ (B $_z$) near point (), m arked by a cross.

in 400 s into the F = 2, m = 2 ground state, and loaded into a large quadrupole trap with x;y;z gradients of 33, 8, and 25 G /cm, respectively. Next, by increasing a bias eld B_z generated by a small coil located 2 mm below the chip, the atom s are com pressed in 300 m s into a Io e m icrotrap, where the conversion from quadrupole to Io e trap geometry follows Ref. [18]. The trap is located at d = 50 m from the surface and 430 m away from the P ribbon along y for currents of 0.6 A in both the Q wires and the P ribbon. For a eld at trap bottom of $B_0 = 1.5 G$, the radial and axial vibration frequencies are $!_{rad}=2 = 5.1 \text{ kHz}$ and $!_{ax}=2 = 70 \text{ Hz}$, respectively. We typically load 3 10° atom s at an initial tem perature of 300 K, peak density of 1:7 10^{2} cm ³, and peak collision rate of 140 s¹. Three seconds of forced evaporation cool the sam ple to below the transition tem perature $T_c = 0.8$ K.W hen the therm alcom ponent is no longer discernible in a tim e-of- ight im age, the condensate contains 10^3 atom s at a peak density of $n_p = 8 \quad 10^{4}$ cm 3 . To measure surface-induced loss, we transport the condensate or a cloud near T_c adiabatically in 40 m s to a de ned position near the surface, hold it there for a variable time, and image the cloud after moving it back to d = 100 m. The noise-equivalent-optical-density of 1% in the absorption imaging corresponds to a small atom num ber noise N = 50 for a condensate. The procedure is repeated for each param eter value.

In order to compare an observed in uence of the surface to theoretical models, the accurate calibration of the trap position (x,z) in the xz plane is crucial. W hile optical imaging fails close to the chip, the calibration is facilitated by the symmetry of the photolithographically de ned Q wires (see Fig. 1). The trap is low

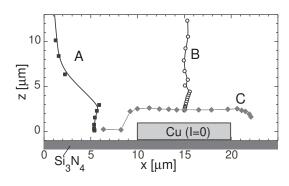


FIG.3: Paths chosen for trap lifetime measurements above a dielectric surface (A) and above a copper lm (B). Line C is the measured contour line of 22 m s lifetime near the metal.

cated where a hom ogeneous external bias eld, with x and z components (B_x, B_z) , cancels the eld from the Q wires. Once the bias eld value (B_x^0, B_z^0) that places the trap at the symmetry center (x=0,z=0) of the Q wires is known precisely, the atoms can be accurately positioned at arbitrary (x,z) by applying an additional eld $(B_x; B_z) = (B_x \quad B_x^0; B_z \quad B_z^0)$ to compensate the spatially varying eld from the Q wires. Fig.2a shows how the relative eld (B_x, B_z) maps to trap position (x,z). We also take into account a slight m ap distortion due to all other coils in the setup, which displaces the Io e trap by 0.50 (5) m away from the chip com pared to the map de ned by the Q wires alone.

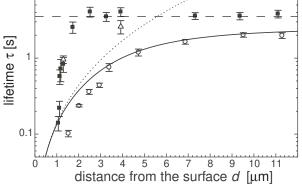
To precisely measure the symmetry-center bias eld (B_x^0, B_z^0) that depends on unknown stray elds, we make use of the relection symmetry of the Q wire con quration. We exploit the fact that a mirror image trap, located at (x, z), coexists with the trap at (x,z) (see Fig. 2a). As the trap and the image trap are brought close, the atom s can overcom e the barrier between the traps, and will be lost if the im age trap is inside the surface. A long a B_z contour, the loss is symmetric about the point $B_x = 0$ (e.g., point in Fig. 2a), where the minimum barrier leads to maximum loss. From the measured atom number versus B $_x$ along the B $_z$ = -120 m G contour, we determ in B_x^0 with a precision of B_x^0 = 4 m G (Fig. 2b). Sim ilarly, B_z^0 is determined within $B_z^0 =$ 10 m G (Fig. 2c) by a measurem ent along the B $_x$ = 110 mG contour near point in Fig. 2a. In the spatial region of interest, the uncertainties $(B_x^0; B_z^0)$ correspond to a trap z position error of 20 nm, sm all com pared to a condensate size of 300 nm in the xz plane.

To verify that we can position the trap accurately relative to microscopic structures on the surface, we rst measure a line of constant lifetime = 22 m s near a C u Im carrying no current, shown as curve C in Fig. 3. This \surface microscopy" yields a contour that displays the expected symmetry about the metal, which con rm s the skewed eld-to-position mapping in Fig. 2a. Fig. 3 also shows the trajectories we then use to measure the lifetim e above the SigN 4 dielectric (A) and the copper Im (B). Path A is selected to avoid coupling to the image trap in the center region.

Fig. 4 shows the lifetime as a function of distance d from the respective surface, measured at T = 1 K $(T=T_c = 1:3)$ for an o set eld B₀ = 0.57 G. The lifetime above the dielectric is constant for d 2:5 m, while above the metal is shorter and distance-dependent. Since even a conductor carrying no macroscopic current generates m agnetic eld uctuations associated with therm al current noise [16], it can induce trap decay by driving transitions from trapped to untrapped atom ic sublevels [15]. In the limit that the metal lm thickness (here t=2.15(20) m) is much smaller than the skin depth at the transition frequency (= 103 m for $B_0 = 0.57 \text{ G}$), the current noise is the Johnson noise in the conductor, and is frequency-independent. (The measurements in Refs. [13, 14] were performed in the , of a bulk metal.) Then for a opposite limit, t metal lm of width w t, and resistivity at tem perature T, the spin ip rate F; mi! F; m 1 i is given by $F_{m} = C_{F_{m}}^{2} C_{0} [d(1 + d=t)(1 + 2d=w))]^{-1}$. This formula interpolates the loss rates predicted by Henkel et w. We derive al. [15] in the limits d w and d _{Fm} at d w from Ref. [15] assuming only thermal currents along the wire contribute substantially. Here 15 F;mif,S is the electron spin $C_{F_m}^2 = \frac{1}{2}F;m$ low ering operator, $C_0 = 88 \text{ s}^{-1} \text{ m}$ $(T/300K)(_{Cu}=),$ $_{Cu} = 1.7$ 10 8 m, T = 400 K from the measured = $_{Cu}$, and w = 10 m. We assume the atom s are lost in a cascade process, $\frac{1}{2}$;2i! $\frac{1}{2}$;1i! $\frac{1}{2}$;0i, replace C_{Fm}^2 by $(C_{22}^{2} + C_{21}^{2})^{1} = (4 + \frac{8}{3})^{1}$, and add the distanceindependent one-body loss rate $_1 = 0.4$ s 1 observed at 10 m. The result (solid line) agrees well with the d observed lifetime above the thin copper lm. For comparison, the fundam ental lim it due to therm al eld noise only $(_1 = 0)$ is plotted as a dotted line. Except for the point closest to the metal surface, is independent of sample temperature, indicating that the loss process is not evaporation at nite trap depth. Further, the lifetime (d) measured for $B_0 = 1.5 \text{ G}$, i.e. at a three times larger transition frequency, is compatible with white eld noise within 40%.

Above the dielectric, the constant lifetim e = 3.5 s observed for d > 2.5 m is independent of cloud tem perature for 1 K T 3 K, and the latter rem ains constant within our resolution of 0.25 K/s. In the short-distance region of decreasing lifetime, however, is longer for a colder cloud, which is consistent with surface-induced 1D evaporation [14, 19]. To test this explanation, we measure the remaining atom fraction after 15 m s versus d for a condensate, and for therm alclouds at 2.1 K and 4.6 K (Fig. 5). A therm alcloud exhibits loss at a larger distance than a condensate, and the latter vanishes at a nite distance d = 1 m.

In the absence of atom -surface interactions, the trap depth would be given by the value of the trapping potential at the surface. However, as shown in the inset to Fig. 5, the attractive Casim in-Polder potential [17], $V_{CP} = C_4 = d^4$, low ers the trap depth, and the trap dis-



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FIG.4: Trap lifetime as a function of distance from a dielectric (solid squares) and m etal (open circles) surface, for T = 1K and $B_0 = 0.57$ G. The dotted line is the calculated lifetime above the metal due to therm al B elds only, the solid line includes the one-body lifetime. The open triangles are m easurem ents for a pure condensate above the dielectric.

appears at nite d. To quantify this e ect, we model the process as a sudden loss of the Boltzm ann tail as the atom s are brought near the surface, in conjunction with 1D evaporation for $t_0 = 15 \text{ m s in a trap with } !_{rad} = 2 =$ 3:6 kHz. The remaining fraction after the sudden loss is given by F = 1 e , where $= U_0 = (kT)$ is the ratio of the Casim in-force limited trap depth U_0 (d) and therm al energy kT.W e account for atom tunneling through the barrier as a small reduction in the e ective trap depth. The loss rate for 1D evaporation is = f()e = el, which using f () = $2^{5=2}$ (1) $\frac{1}{2} + \frac{3}{2}$ ²) is accurate to 5% for 4 [20]. G iven elastic collision times $e_1 = 0.2$ m s, 0.9 m s, and 1.5 m s for the condensate, the 2.1 K and the 4.6 K clouds, respectively, we plot in Fig. 5 the remaining fraction $_{CP}$ = Fe t_0 . For the condensate, we assume that the loss is due to collisions between a residual therm all cloud at $T_c=2$ and the condensate. For the Casim ir potential we use the coe cient (") $3hc = (32_{0}^{2})$, where $= 5.25_{10}^{39}$ Fm² is C₄ = the Rb polarizability, and (") = 0.46(5) is a num erical factor from Ref. [21] for the Si₃N₄ dielectric constant of " = 4.0(8). For com parison, we also plot the calculated fraction in the absence of any surface potential ($C_4 = 0$).

Fig. 5 can be interpreted as a measurement of the Casim in-Polder coe cient C $_4$ that is, however, lim ited by the uncertainty of the distance calibration. The dom inant contribution of 100 nm arises from a 200 nm uncertainty of the conductor thickness t (see Fig. 2). In addition, an estim ated 10% eld calibration uncertainty for B x contributes a 10% scaling error about the distance $d_0 = 1.6$ m. Furtherm ore, our setup with a 1 m Si₃N₄ layer on Si is a dielectric wavequide. The corresponding correction to C_4 com pared to a Si_3N_4 half-space is estimated to be less than 20% [22]. Uncertainties in tem perature and trap vibration frequency of 10% also

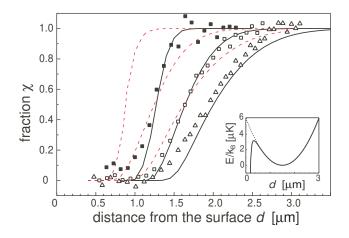


FIG. 5: Remaining atom fraction in a trap at distance d from dielectric surface for a condensate (solid squares), and for therm alclouds at 2.1 K (open squares) and 4.6 K (triangles). The solid (dashed) lines are calculated with (without) C asim ir-Polder potential for the BEC, 2.1 K, 4.6 K clouds (left to right). The inset shows the trapping potentials for $C_4 = 82 \quad 10^{-56}$ Jm⁴ (solid line) and $C_4 = 0$ (dotted line).

a ect $_{CP}$ (d). When we take these error sources into account, our measurements in combination with the 1D evaporation model imply a 66 % condence range for C₄ between 1.2 10⁵⁶ Jm⁴ and 41 10⁵⁶ Jm⁴, which in-

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cludes the nom inal value $C_4 = 82$ 10 ⁵⁶ Jm⁴. The good agreem ent between our data and the predicted C_4 without any adjustment of parameters suggests that the C asim irpotential lim its the trap depth, and consequently lifetime, at small distances d 2 m from the dielectric surface. The discrepancy at small fraction is probably due to our simple 1D evaporation model which breaks down for 1, and also ignores evaporation-induced temperature changes. Our data exclude $C_4 = 0$, even if we allow for the largest possible system atic error.

In conclusion, we have characterized the stability of m agnetically trapped ultracold atoms at m distances from a copper lm and a dielectric surface. The condensate is stable over the dielectric, and the spectral density of the therm alm agnetic eld near a m et al lm scales with m et al thickness. Therefore it will be possible to bring a stable ultracold cloud su ciently close to the surface for the trapping potential to be locally m anipulated.

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Note added : The Casim ir potential cannot explain the anom abusly short lifetime at the smallest distance d = 1.5 m above the metal (see Fig. 4 and the \surface microscopy" curve C in Fig. 3). One possible explanation is patch potentials from Rb atom s adsorbed on the metal, as recently reported by M oG uirk et al. [23].

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